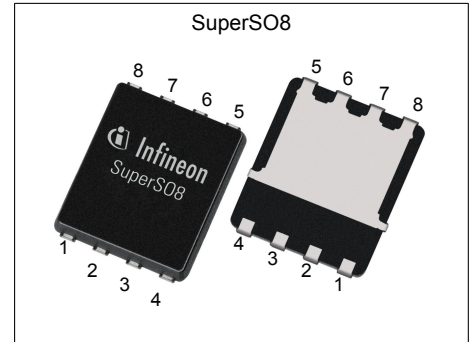


# MOSFET

## OptiMOS™ Power-Transistor, 60 V

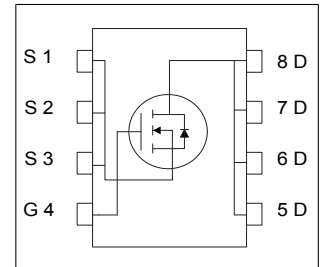
### Features

- Optimized for high performance SMPS, e.g. sync. rec.
- 100% avalanche tested
- Superior thermal resistance
- N-channel
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21



**Table 1 Key Performance Parameters**

| Parameter        | Value | Unit |
|------------------|-------|------|
| $V_{DS}$         | 60    | V    |
| $R_{DS(on),max}$ | 2.8   | mΩ   |
| $I_D$            | 132   | A    |
| $Q_{oss}$        | 43    | nC   |
| $Q_G(0..10V)$    | 37    | nC   |



RoHS

| Type / Ordering Code | Package    | Marking  | Related Links |
|----------------------|------------|----------|---------------|
| BSC028N06NS          | PG-TDSON-8 | 028N06NS | -             |

<sup>1)</sup> J-STD20 and JESD22

## Table of Contents

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## 1 Maximum ratings

at  $T_A=25\text{ °C}$ , unless otherwise specified

**Table 2 Maximum ratings**

| Parameter                                    | Symbol            | Values |      |                 | Unit | Note / Test Condition   |
|--|-------------------|--------|------|-----------------|------|---|
|  |                   | Min.   | Typ. | Max.            |      |   |
| Continuous drain current <sup>1)</sup>       | $I_D$             | -      | -    | 132<br>83<br>23 | A    | $V_{GS}=10\text{ V}$ , $T_C=25\text{ °C}$<br>$V_{GS}=10\text{ V}$ , $T_C=100\text{ °C}$<br>$V_{GS}=10\text{ V}$ , $T_A=25\text{ °C}$ , $R_{thJA}=50\text{K/W}^2)$ |
| Pulsed drain current <sup>3)</sup>           | $I_{D,pulse}$     | -      | -    | 528             | A    | $T_C=25\text{ °C}$  |
| Avalanche energy, single pulse <sup>4)</sup> | $E_{AS}$          | -      | -    | 100             | mJ   | $I_D=50\text{ A}$ , $R_{GS}=25\text{ }\Omega$   |
| Gate source voltage                          | $V_{GS}$          | -20    | -    | 20              | V    | -   |
| Power dissipation                            | $P_{tot}$         | -      | -    | 83<br>2.5       | W    | $T_C=25\text{ °C}$<br>$T_A=25\text{ °C}$ , $R_{thJA}=50\text{ K/W}^3)$  |
| Operating and storage temperature            | $T_j$ , $T_{stg}$ | -55    | -    | 150             | °C   | IEC climatic category;<br>DIN IEC 68-1: 55/150/56   |

## 2 Thermal characteristics

**Table 3 Thermal characteristics**

| Parameter   | Symbol     | Values |      |      | Unit | Note / Test Condition |
|---|------------|--------|------|------|------|-----------------------|
|   |            | Min.   | Typ. | Max. |      |                       |
| Thermal resistance, junction - case, bottom                 | $R_{thJC}$ | -      | 0.9  | 1.5  | K/W  | -                     |
| Thermal resistance, junction - case, top                    | $R_{thJC}$ | -      | -    | 20   | K/W  | -                     |
| Device on PCB, 6 cm <sup>2</sup> cooling area <sup>2)</sup> | $R_{thJA}$ | -      | -    | 50   | K/W  | -                     |

<sup>1)</sup> Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature at 25°C. For higher case temperature please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

<sup>3)</sup> See Diagram 3 for more detailed information

<sup>4)</sup> See Diagram 13 for more detailed information

### 3 Electrical characteristics

at  $T_j=25\text{ °C}$ , unless otherwise specified

**Table 4 Static characteristics**

| Parameter                        | Symbol        | Values |            |            | Unit             | Note / Test Condition   |
|----------------------------------|---------------|--------|------------|------------|------------------|---|
|                                  |               | Min.   | Typ.       | Max.       |                  |   |
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | 60     | -          | -          | V                | $V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$   |
| Gate threshold voltage           | $V_{GS(th)}$  | 2.1    | 2.8        | 3.3        | V                | $V_{DS}=V_{GS}$ , $I_D=50\text{ }\mu\text{A}$   |
| Zero gate voltage drain current  | $I_{DSS}$     | -      | 0.5<br>10  | 1<br>100   | $\mu\text{A}$    | $V_{DS}=60\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ °C}$<br>$V_{DS}=60\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=125\text{ °C}$ |
| Gate-source leakage current      | $I_{GSS}$     | -      | 10         | 100        | nA               | $V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$  |
| Drain-source on-state resistance | $R_{DS(on)}$  | -      | 2.5<br>3.4 | 2.8<br>4.2 | $\text{m}\Omega$ | $V_{GS}=10\text{ V}$ , $I_D=50\text{ A}$<br>$V_{GS}=6\text{ V}$ , $I_D=12.5\text{ A}$   |
| Gate resistance <sup>1)</sup>    | $R_G$         | -      | 1.3        | 1.95       | $\Omega$         | -   |
| Transconductance                 | $g_{fs}$      | 50     | 100        | -          | S                | $ V_{DS} >2 I_D R_{DS(on)max}$ , $I_D=50\text{ A}$  |

**Table 5 Dynamic characteristics**

| Parameter                                  | Symbol       | Values |      |      | Unit | Note / Test Condition  |
|--|--------------|--------|------|------|------|--|
|  |              | Min.   | Typ. | Max. |      |  |
| Input capacitance <sup>1)</sup>            | $C_{iss}$    | 2025   | 2700 | 3375 | pF   | $V_{GS}=0\text{ V}$ , $V_{DS}=30\text{ V}$ , $f=1\text{ MHz}$                                    |
| Output capacitance <sup>1)</sup>           | $C_{oss}$    | 495    | 660  | 825  | pF   | $V_{GS}=0\text{ V}$ , $V_{DS}=30\text{ V}$ , $f=1\text{ MHz}$                                    |
| Reverse transfer capacitance <sup>1)</sup> | $C_{rss}$    | 8.5    | 28   | 56   | pF   | $V_{GS}=0\text{ V}$ , $V_{DS}=30\text{ V}$ , $f=1\text{ MHz}$                                    |
| Turn-on delay time                         | $t_{d(on)}$  | -      | 11   | 22   | ns   | $V_{DD}=30\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=50\text{ A}$ ,<br>$R_{G,ext}=3\text{ }\Omega$ |
| Rise time                                  | $t_r$        | -      | 38   | 57   | ns   | $V_{DD}=30\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=50\text{ A}$ ,<br>$R_{G,ext}=3\text{ }\Omega$ |
| Turn-off delay time                        | $t_{d(off)}$ | -      | 19   | 38   | ns   | $V_{DD}=30\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=50\text{ A}$ ,<br>$R_{G,ext}=3\text{ }\Omega$ |
| Fall time                                  | $t_f$        | -      | 8    | 16   | ns   | $V_{DD}=30\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=50\text{ A}$ ,<br>$R_{G,ext}=3\text{ }\Omega$ |

**Table 6 Gate charge characteristics<sup>2)</sup>**

| Parameter                    | Symbol        | Values |      |      | Unit | Note / Test Condition   |
|------------------------------|---------------|--------|------|------|------|---|
|                              |               | Min.   | Typ. | Max. |      |   |
| Gate to source charge        | $Q_{gs}$      | 9      | 12   | 16.5 | nC   | $V_{DD}=30\text{ V}$ , $I_D=50\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate charge at threshold     | $Q_{g(th)}$   | 6      | 8    | 11   | nC   | $V_{DD}=30\text{ V}$ , $I_D=50\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate to drain charge         | $Q_{gd}$      | 5      | 7    | 10.3 | nC   | $V_{DD}=30\text{ V}$ , $I_D=50\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Switching charge             | $Q_{sw}$      | 8      | 12   | 17   | nC   | $V_{DD}=30\text{ V}$ , $I_D=50\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate charge total            | $Q_g$         | 31     | 37   | 49   | nC   | $V_{DD}=30\text{ V}$ , $I_D=50\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate plateau voltage         | $V_{plateau}$ | 4.0    | 4.6  | 5.2  | V    | $V_{DD}=30\text{ V}$ , $I_D=50\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate charge total, sync. FET | $Q_{g(sync)}$ | 27     | 33   | 43   | nC   | $V_{DS}=0.1\text{ V}$ , $V_{GS}=0\text{ to }10\text{ V}$                    |
| Output charge                | $Q_{oss}$     | 32     | 43   | 54   | nC   | $V_{DD}=30\text{ V}$ , $V_{GS}=0\text{ V}$                                  |

<sup>1)</sup> Defined by design. Not subject to production test

<sup>2)</sup> See "Gate charge waveforms" for parameter definition. Defined by design, not subject to production test

**Table 7 Reverse diode**

| Parameter                             | Symbol        | Values |      |      | Unit | Note / Test Condition  |
|---------------------------------------|---------------|--------|------|------|------|--|
|                                       |               | Min.   | Typ. | Max. |      |  |
| Diode continuous forward current      | $I_S$         | -      | -    | 100  | A    | $T_C=25\text{ °C}$   |
| Diode pulse current                   | $I_{S,pulse}$ | -      | -    | 528  | A    | $T_C=25\text{ °C}$   |
| Diode forward voltage                 | $V_{SD}$      | -      | 0.9  | 1.2  | V    | $V_{GS}=0\text{ V}, I_F=50\text{ A}, T_j=25\text{ °C}$               |
| Reverse recovery time <sup>1)</sup>   | $t_{rr}$      | 14     | 35   | 56   | ns   | $V_R=30\text{ V}, I_F=50\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$ |
| Reverse recovery charge <sup>1)</sup> | $Q_{rr}$      | 14     | 29   | 58   | nC   | $V_R=30\text{ V}, I_F=50\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$ |

<sup>1)</sup> Defined by design. Not subject to production test

### 4 Electrical characteristics diagrams

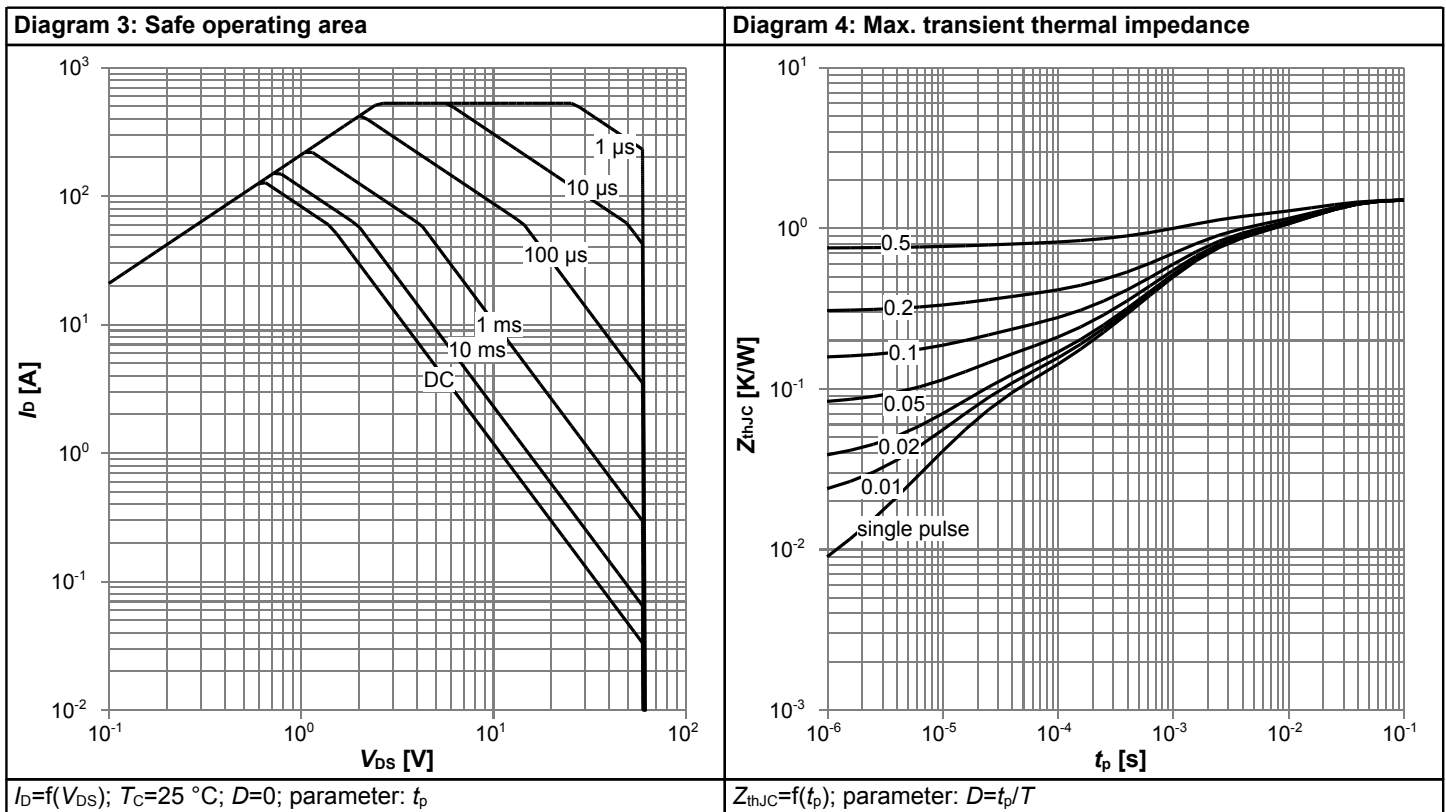
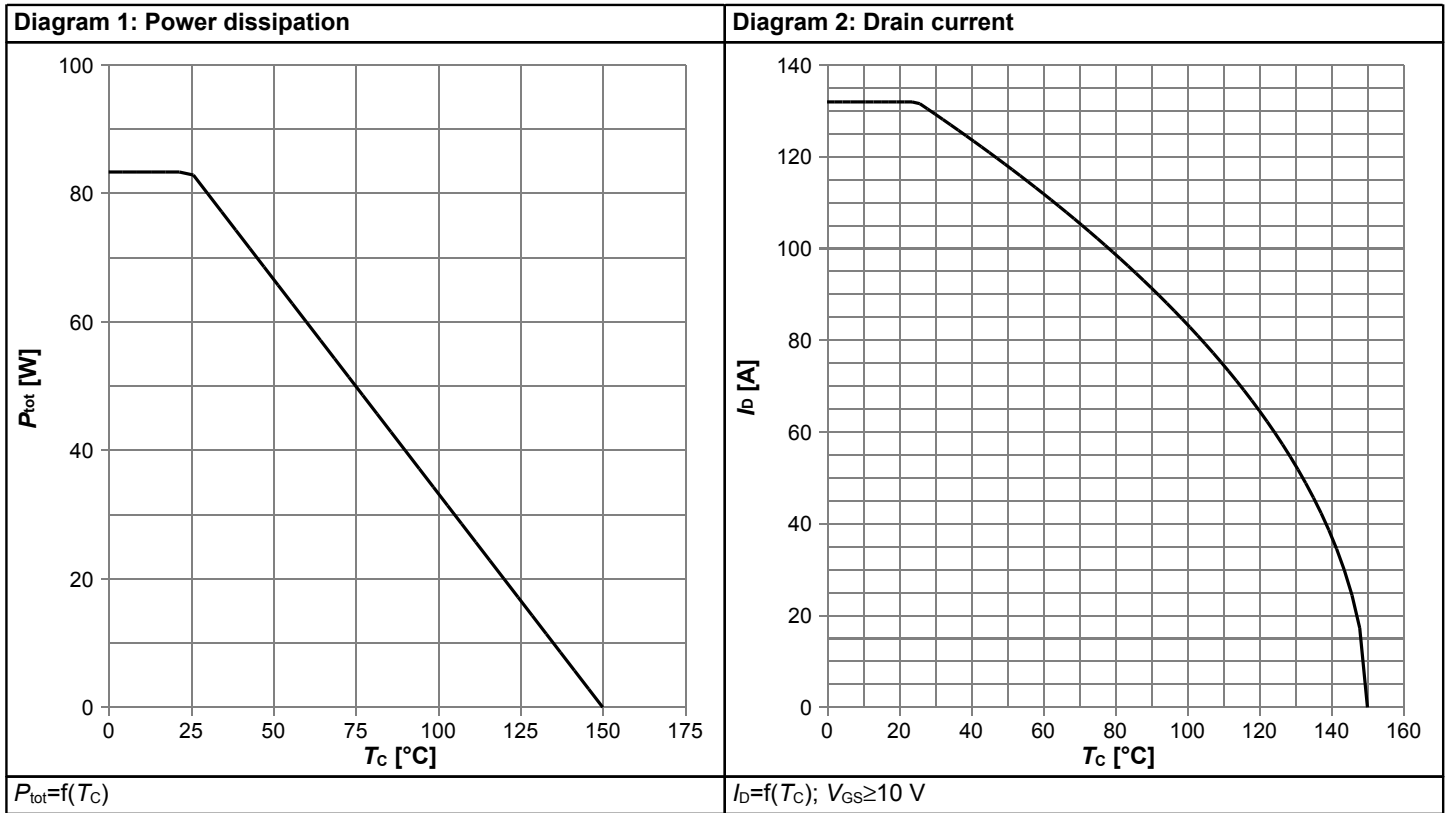
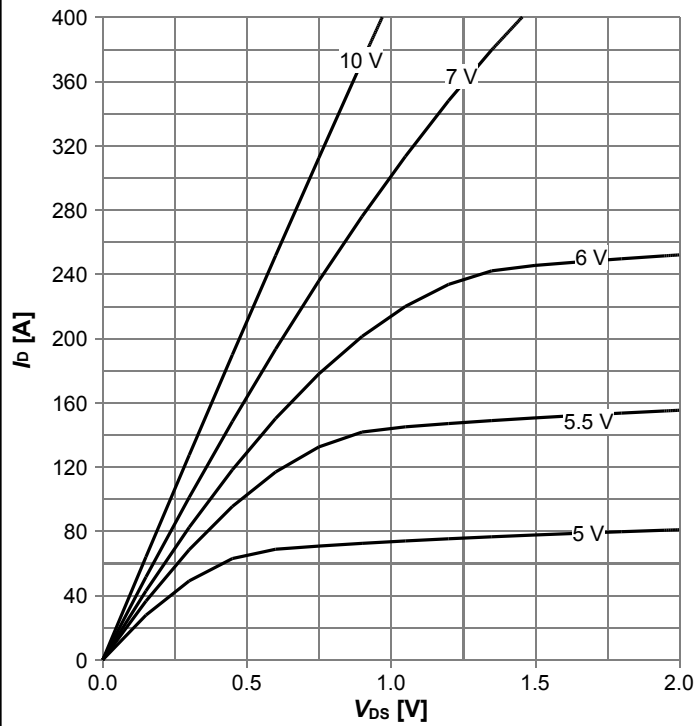
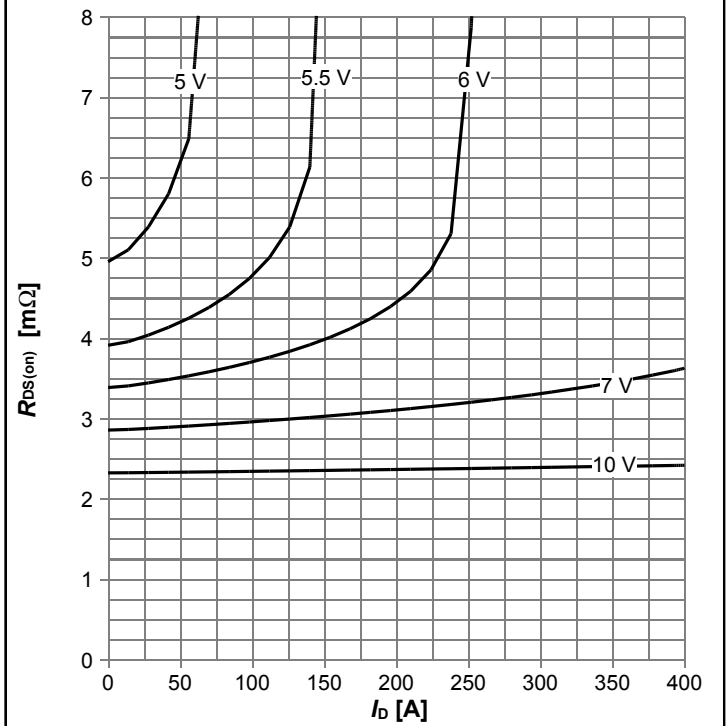


Diagram 5: Typ. output characteristics



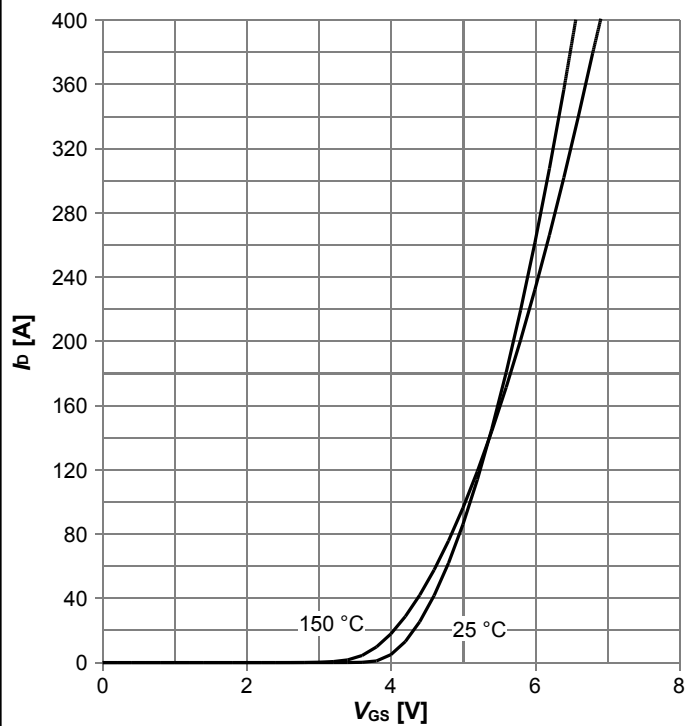
$I_D=f(V_{DS})$ ;  $T_j=25\text{ }^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 6: Typ. drain-source on resistance



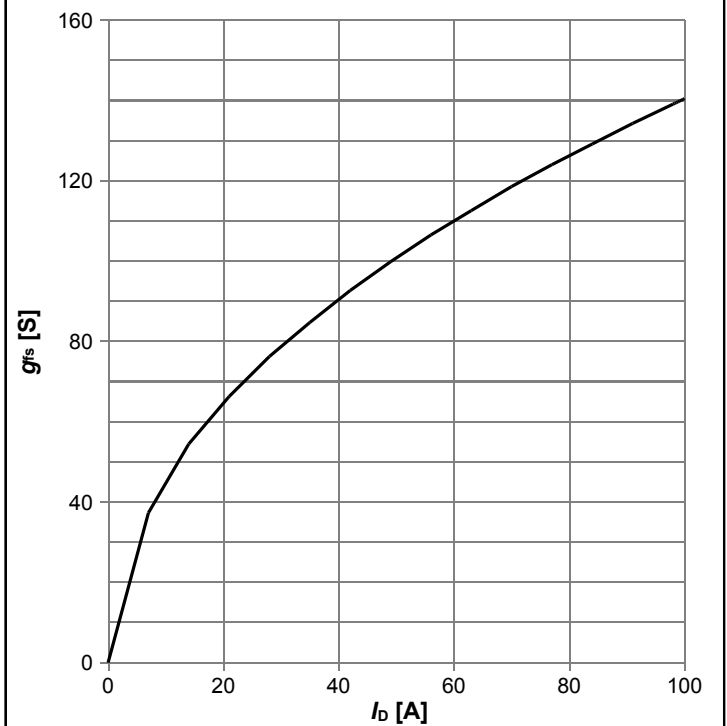
$R_{DS(on)}=f(I_D)$ ;  $T_j=25\text{ }^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 7: Typ. transfer characteristics



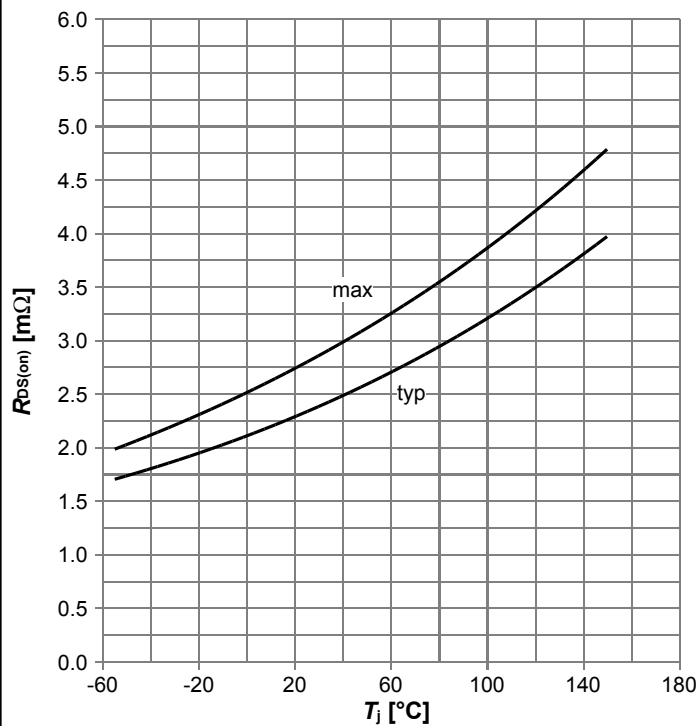
$I_D=f(V_{GS})$ ;  $|V_{DS}|>2|I_D|R_{DS(on)max}$ ; parameter:  $T_j$

Diagram 8: Typ. forward transconductance



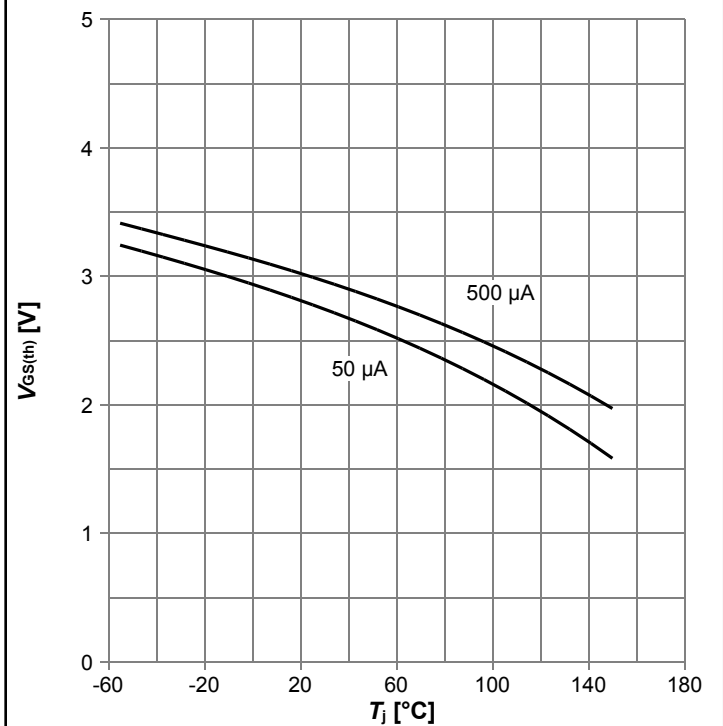
$g_{fs}=f(I_D)$ ;  $T_j=25\text{ }^\circ\text{C}$

Diagram 9: Drain-source on-state resistance



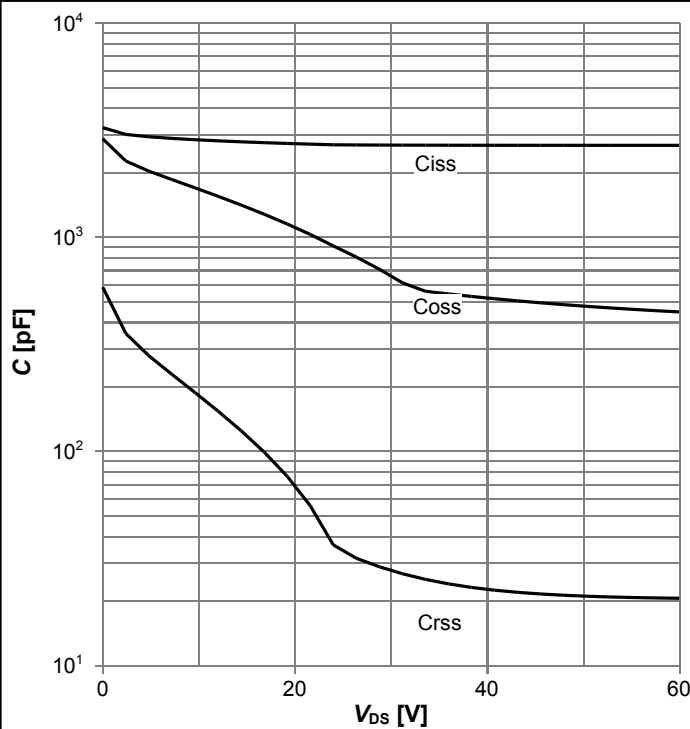
$R_{DS(on)}=f(T_j)$ ;  $I_D=50$  A;  $V_{GS}=10$  V

Diagram 10: Typ. gate threshold voltage



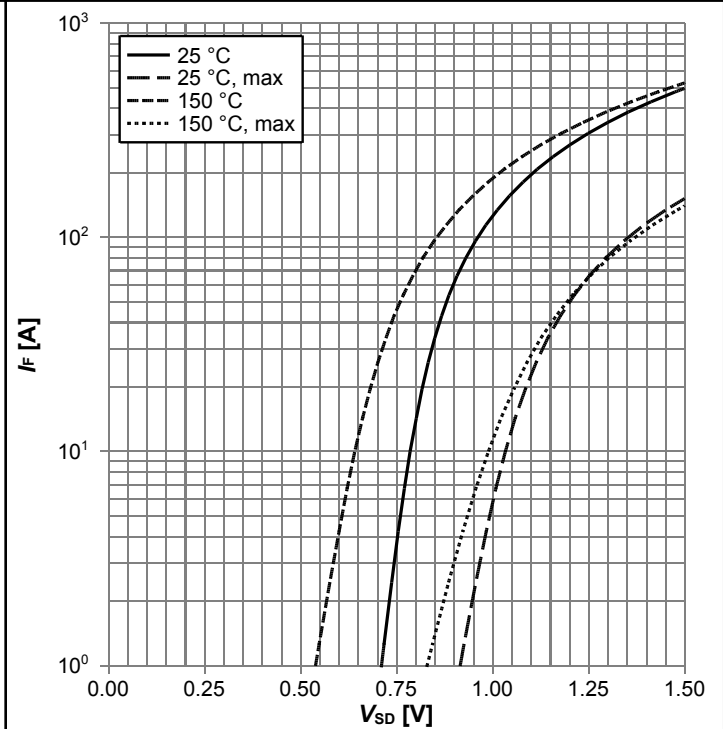
$V_{GS(th)}=f(T_j)$ ;  $V_{GS}=V_{DS}$

Diagram 11: Typ. capacitances



$C=f(V_{DS})$ ;  $V_{GS}=0$  V;  $f=1$  MHz

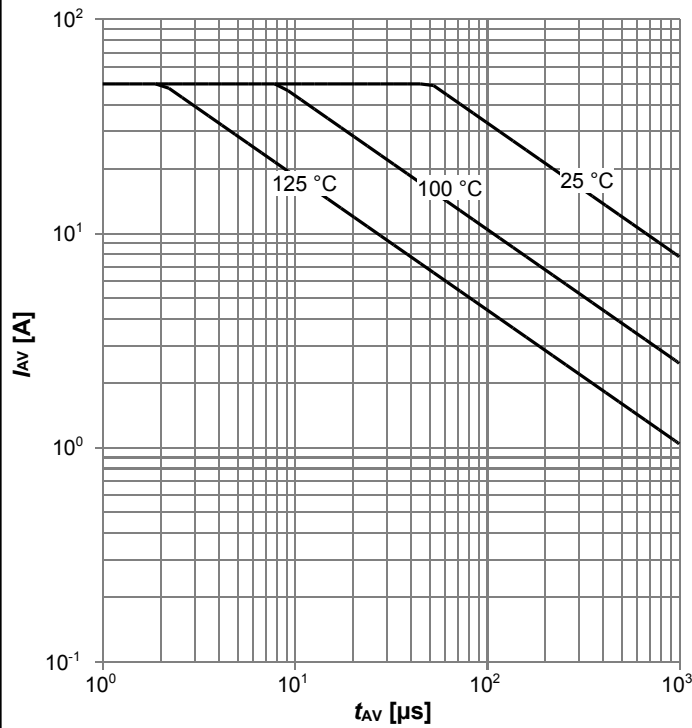
Diagram 12: Forward characteristics of reverse diode



$I_F=f(V_{SD})$ ; parameter:  $T_j$

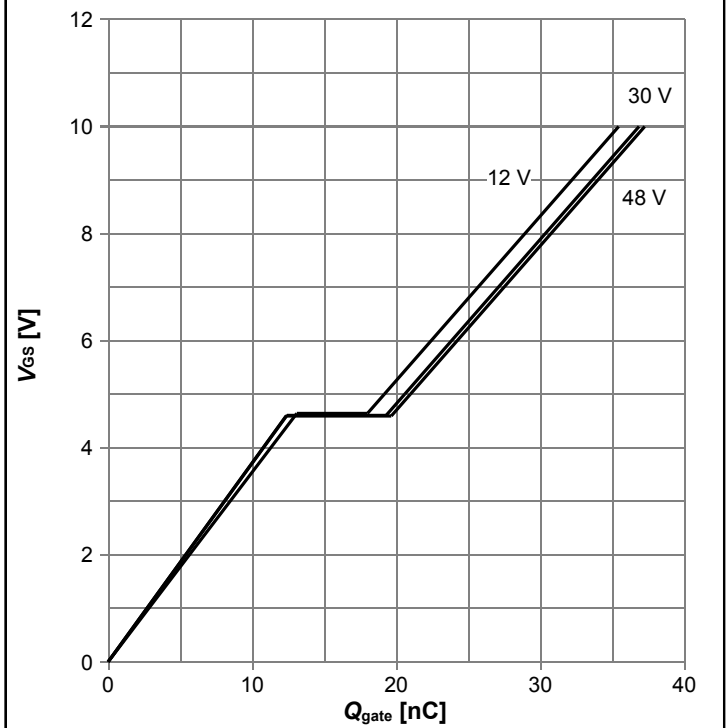


Diagram 13: Avalanche characteristics



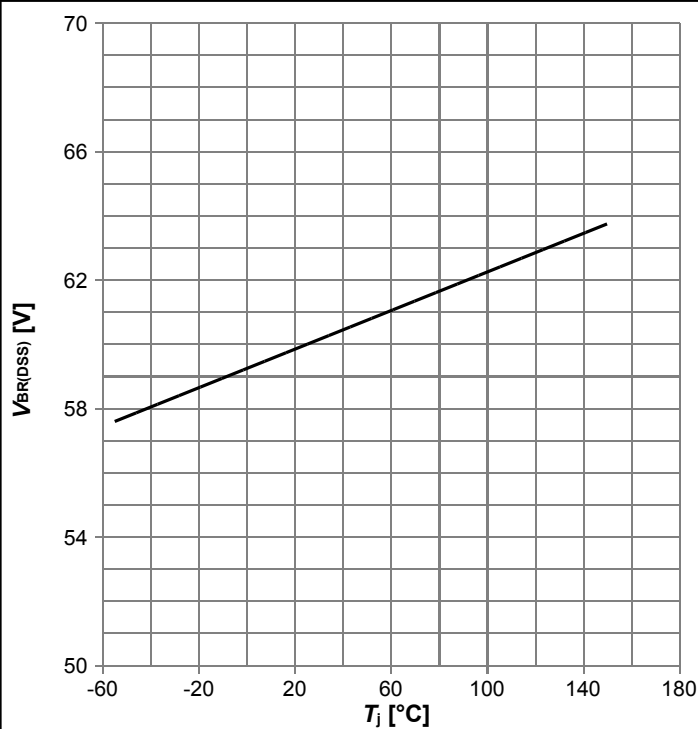
$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$ ; parameter:  $T_{j(start)}$

Diagram 14: Typ. gate charge



$V_{GS}=f(Q_{gate}); I_D=50 \text{ A pulsed}$ ; parameter:  $V_{DD}$

Diagram 15: Drain-source breakdown voltage



$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

Diagram Gate charge waveforms



## 5 Package Outlines



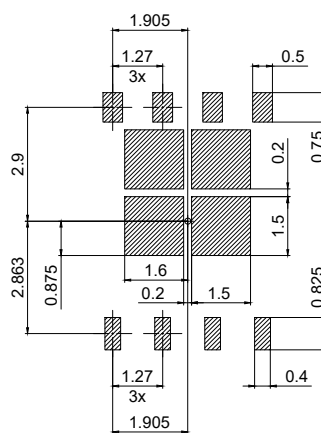
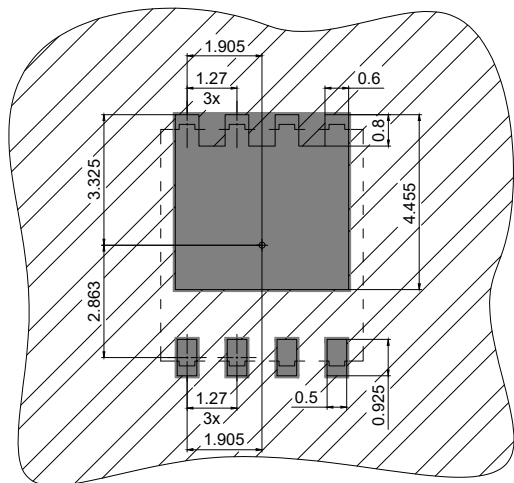
- 1) EXCLUDING MOLD FLASH
- 2) REMOVAL ON MOLD GATE  
INTRUSION 0.1 MM  
PROTRUSION 0.1 MM  
LEAD LENGTH UP TO ANTI FLASH LINE  
ALL METAL SURFACES ARE PLATED, EXCEPT AREA OF CUT

| DIMENSION | MILLIMETERS |      |
|-----------|-------------|------|
|           | MIN.        | MAX. |
| A         | 0.90        | 1.20 |
| A1        | 0.15        | 0.35 |
| b         | 0.34        | 0.54 |
| D         | 4.80        | 5.35 |
| D1        | 3.90        | 4.40 |
| D2        | 0.03        | 0.23 |
| E         | 5.70        | 6.10 |
| E1        | 5.90        | 6.42 |
| E2        | 3.88        | 4.31 |
| e         | 1.27        |      |
| L         | 0.45        | 0.71 |
| M         | 0.45        | 0.69 |

|                                    |
|------------------------------------|
| <b>DOCUMENT NO.</b><br>Z8B00003332 |
| <b>REVISION</b><br>07              |
| <b>SCALE 10:1</b><br>0 1 2 3mm     |
| <b>EUROPEAN PROJECTION</b><br>     |
| <b>ISSUE DATE</b><br>06.06.2019    |

Figure 1 Outline PG-TDSON-8, dimensions in mm

PG-TDSON-8: Recommended Boardpads & Apertures



■ copper

▨ solder mask

▨ stencil apertures

all dimensions in mm

Figure 2 Outline Boardpads (TDSON-8), dimensions in mm



## Revision History

BSC028N06NS

Revision: 2020-09-21, Rev. 2.5

### Previous Revision

| Revision | Date       | Subjects (major changes since last revision)   |
|----------|------------|--|
| 2.3      | 2014-11-10 | Added RthJC_typ, updated outline and footprint drawings, insert footnote "Defined by design...." |
| 2.4      | 2020-02-04 | Update package drawings  |
| 2.5      | 2020-09-21 | Update current rating  |

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